

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Priority Application Serial No. 10/241,923
 Priority Filing Date September 11, 2002
 Inventor David L. Dickerson et al.
 Assignee Micron Technology, Inc.
 Priority Group Art Unit 2814
 Priority Examiner A.D. Mai
 Attorney's Docket No. MI22-2500
 Title: Isolation Region Forming Methods

INFORMATION DISCLOSURE STATEMENT

References - - See attached Form PTO-1449

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449. No admission is made regarding whether all the submitted references are prior art.

The listed references were cited by, or submitted to, the Office in the parent, co-pending application of the above-identified application. The above-identified application is a continuation application of co-pending application Serial No. 10/241,923, filed September 11, 2002, upon which the above-identified application relies for a priority date under 35 U.S.C. §120. Such prior disclosure is sufficient for the above-identified application as far as copies of the references are concerned. 37 C.F.R. §1.98(d) and MPEP §609(2). As a courtesy, Applicant submits copies of the cited foreign references and articles (**ONLY**) for review.

Citation of these references is respectfully requested.

Respectfully submitted,

Date: 3-11-04



D. Brent Kenady
 Reg. No. 40,045

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. M122-2500		SERIAL NO. Filed Herewith	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)					APPLICANT David L. Dickerson et al.			
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EXAMINER				DATE CONSIDERED				
<small>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>								

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	AT		Fazan & Mathews, "A Highly Manufacturable Trench Isolation Process for Deep Submicron DRAMs," IEEE 1993, 4 pages.				
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	AR						
	AS						
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	AU						
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